

T7070U-VNG2 High Power UV LED

Introduction

The T7070U-VNG2 product is a compact, high quality and reliable 4-chip UV LED with 60 degree quartz glass lens. Featuring high radiometric power density and design flexibility - the T7070U-VNG2 spectrum can be tailored to your printer, inkjet, glue adhesive curing, and PCB lithography applications.



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RoHS Compliant

Characteristics

Absolute Maximum Ratings ($T_j = 25^\circ\text{C}$)

Parameter	Rating
	UV Series
DC Forward Current (mA)	700 mA
LED Junction Temperature	150°C
LED Operating Temperature	-40°C ~ 85°C
Storage Temperature	-40°C ~ 125°C
Soldering Temperature	Max. 260°C / Max. 10sec. (JEDEC 020c)
ESD Sensitivity	2,000 V HBM (JESD-22A-114-B)
Reverse Voltage	Not designed to be driven in reverse bias ($V_R \leq 5V$)
Preconditioning	Acc. to JEDEC Level 2

General Characteristics at 700mA

Part number	Color	Peak Wavelength λ_p		$2\theta_{1/2}$	Temperature Coefficient of V_f (mV/°C)	Thermal Resistance Junction to Pad
		Min	Max			
T7070U-VNG2-A1J41H	U2B	365	370	65	-17	3.2
	U3A	370	375	65	-17	3.2

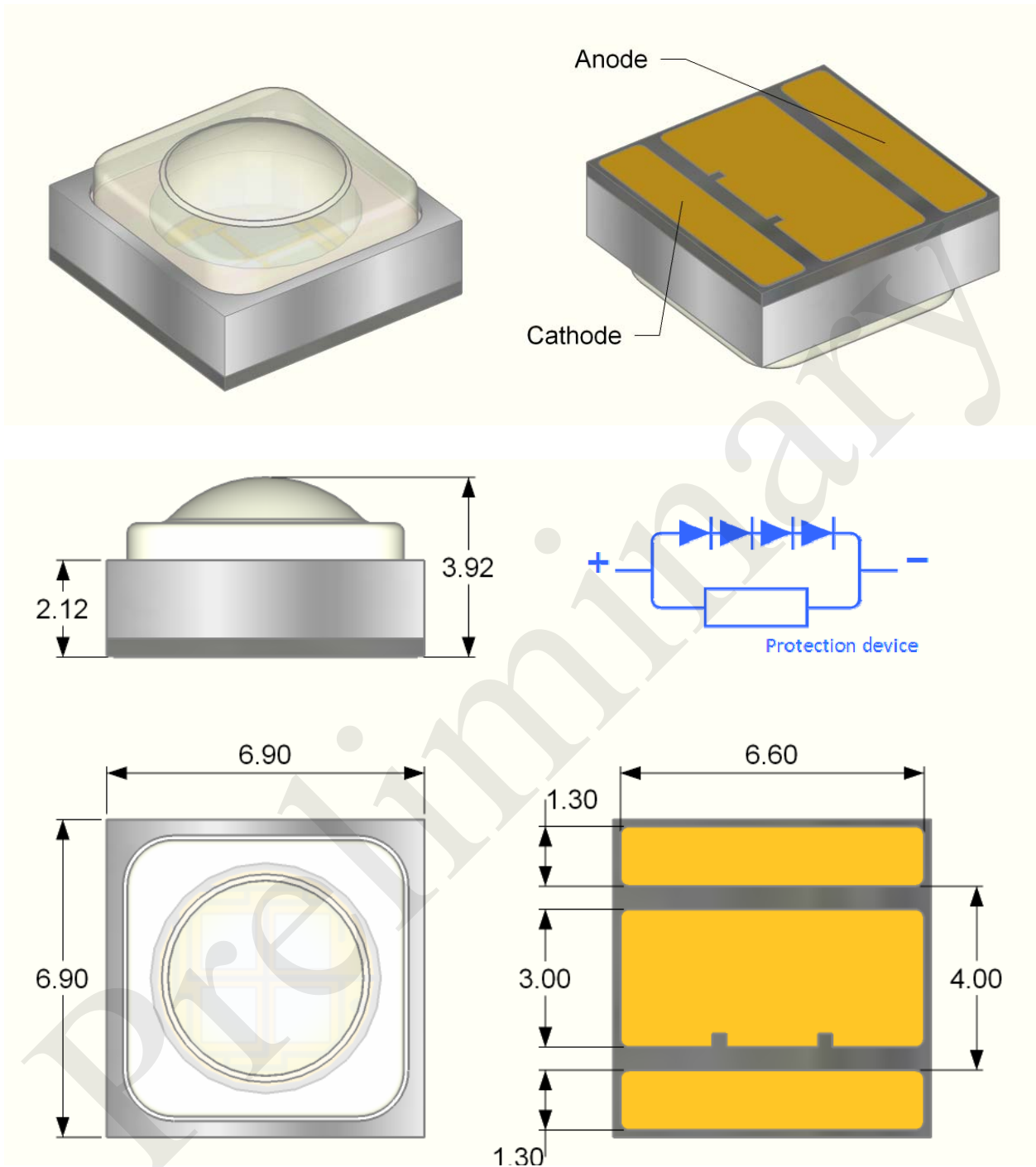
Notes: The peak/dominant wavelength is measured with an accuracy of $\pm 1\text{nm}$

Radiometric Power and Forward Voltage ($T_j = 25^\circ\text{C}$)

Part number	Color	Performance at Test Current (700mA)			
		Group	Minimum Radiometric Power (mW)	VF	
				Min	Max
T7070U-VNG2-A1J41H	U2B (365-370nm)	NH3	1200	13	17
		NH4	1300	13	17
		NH5	1400	13	17
		NH6	1500	13	17
		NH7	1600	13	17
	U3A (370-375nm)	NH3	1200	13	17
		NH4	1300	13	17
		NH5	1400	13	17
		NH6	1500	13	17
		NH7	1600	13	17

- Note: 1. Radiometric power is measured with an accuracy of $\pm 10\%$
 2. The forward voltage is measured with an accuracy of $\pm 0.1\text{V}$

Mechanical Dimensions

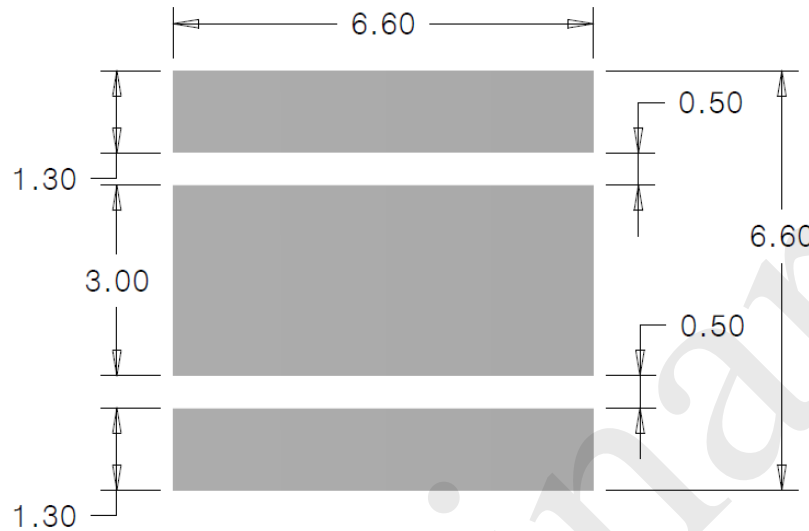


Notes:

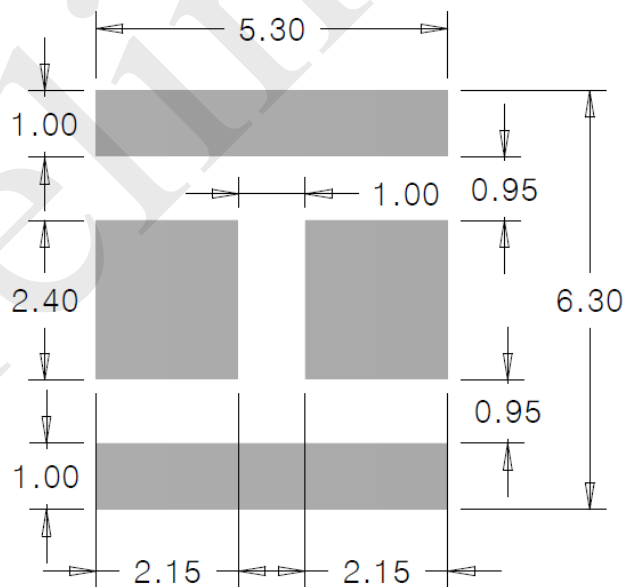
1. Drawing is not to scale
2. All dimensions are in millimeter
3. Dimensions are $\pm 0.13\text{mm}$ unless otherwise indicated

Recommended Solder Pad Design

Recommended Soldering Pad Design



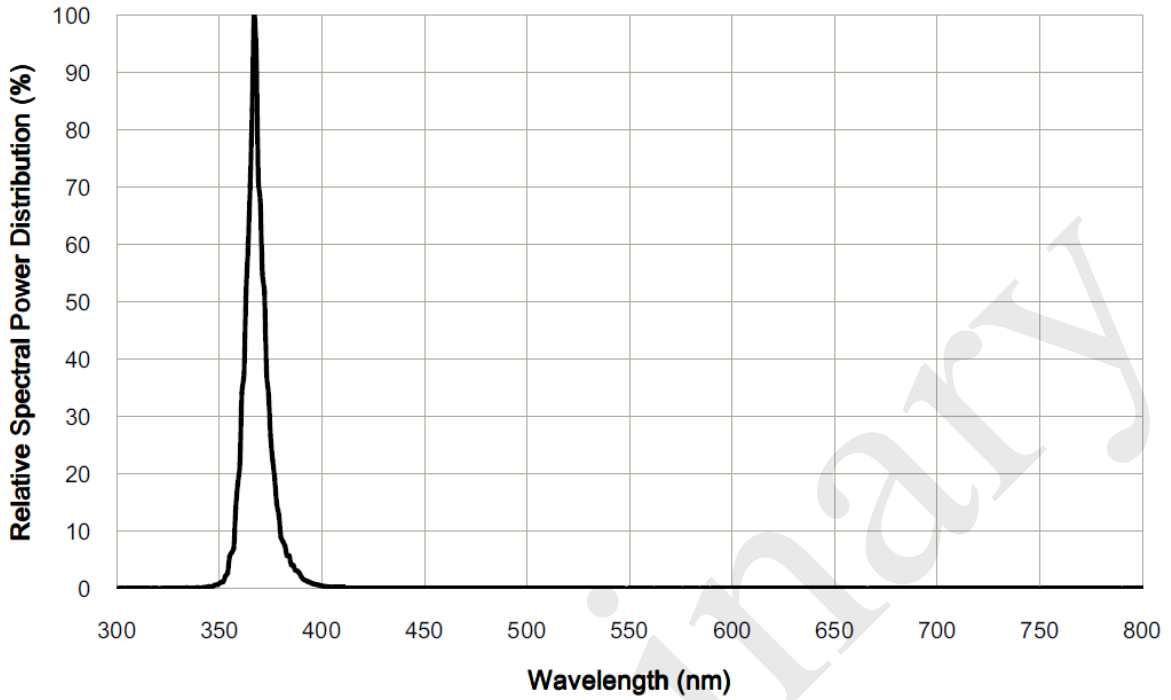
Recommended Stencil Pattern Design (Marked Area is Opening)



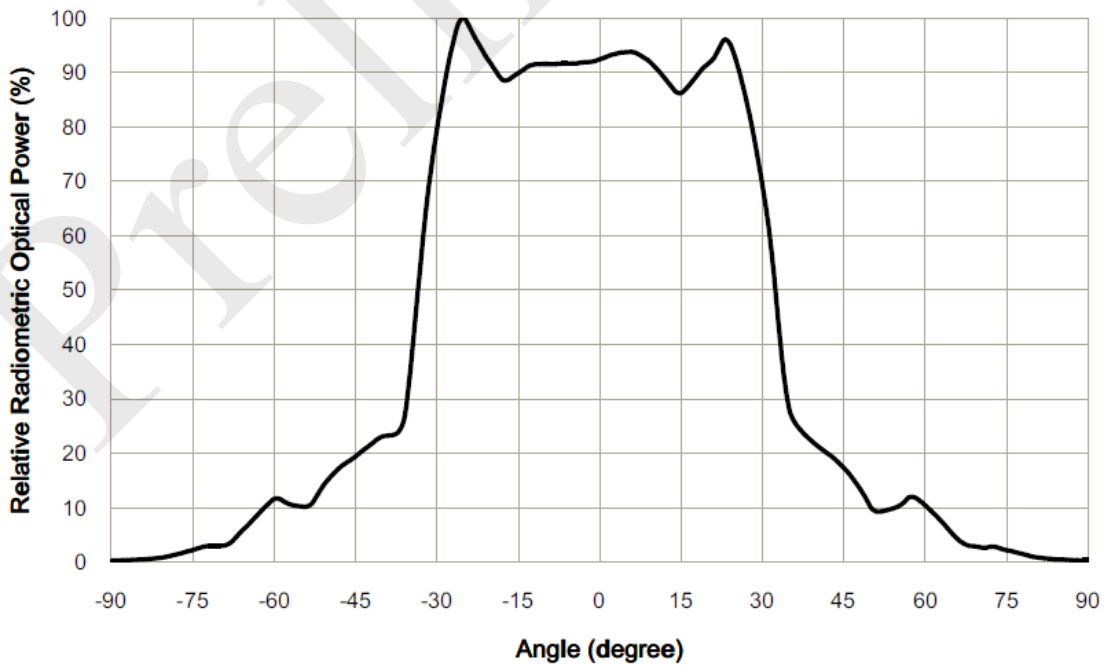
Notes:

1. Drawing is not to scale
2. All dimensions are in millimeter

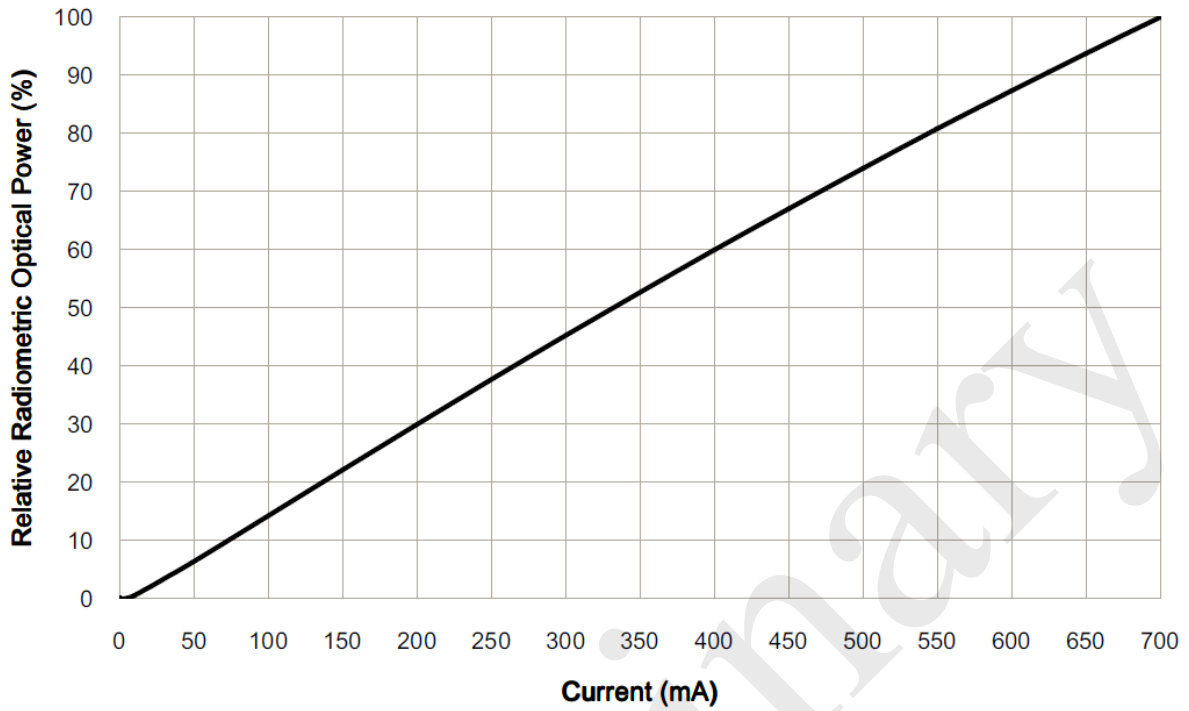
Relative Spectral Power Distribution, $T_j=25^\circ\text{C}$



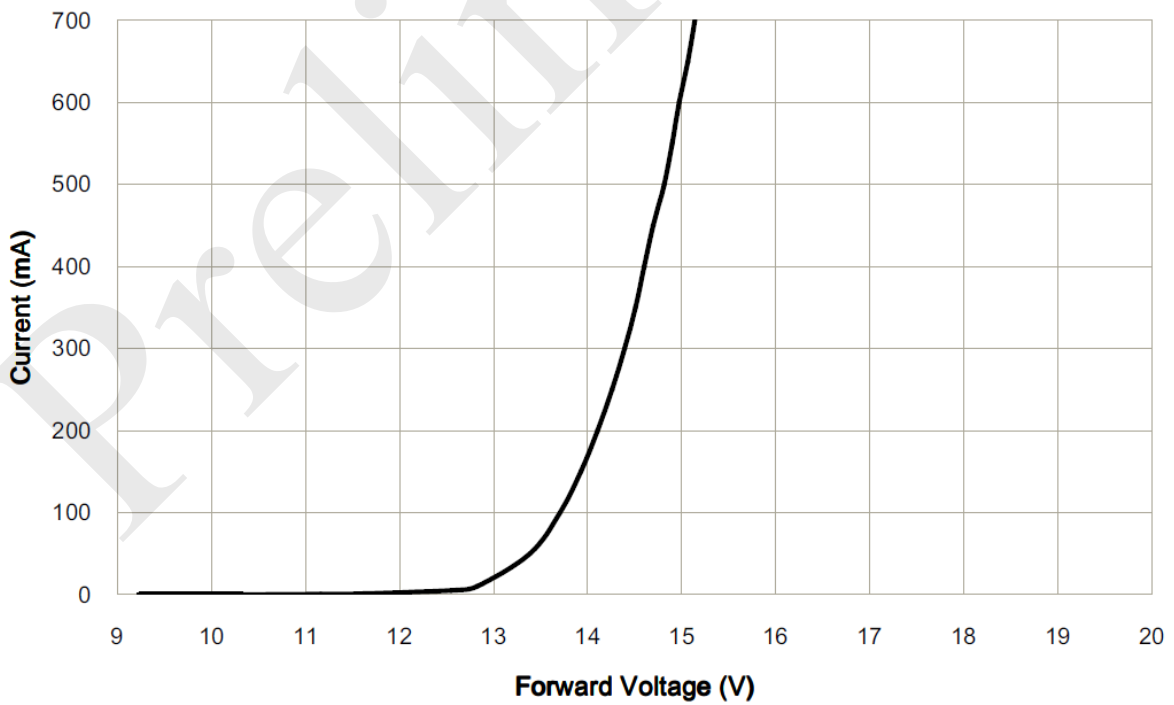
Typical Spatial Radiation Pattern



Typical Forward L-I Characteristics, $T_j=25^\circ\text{C}$

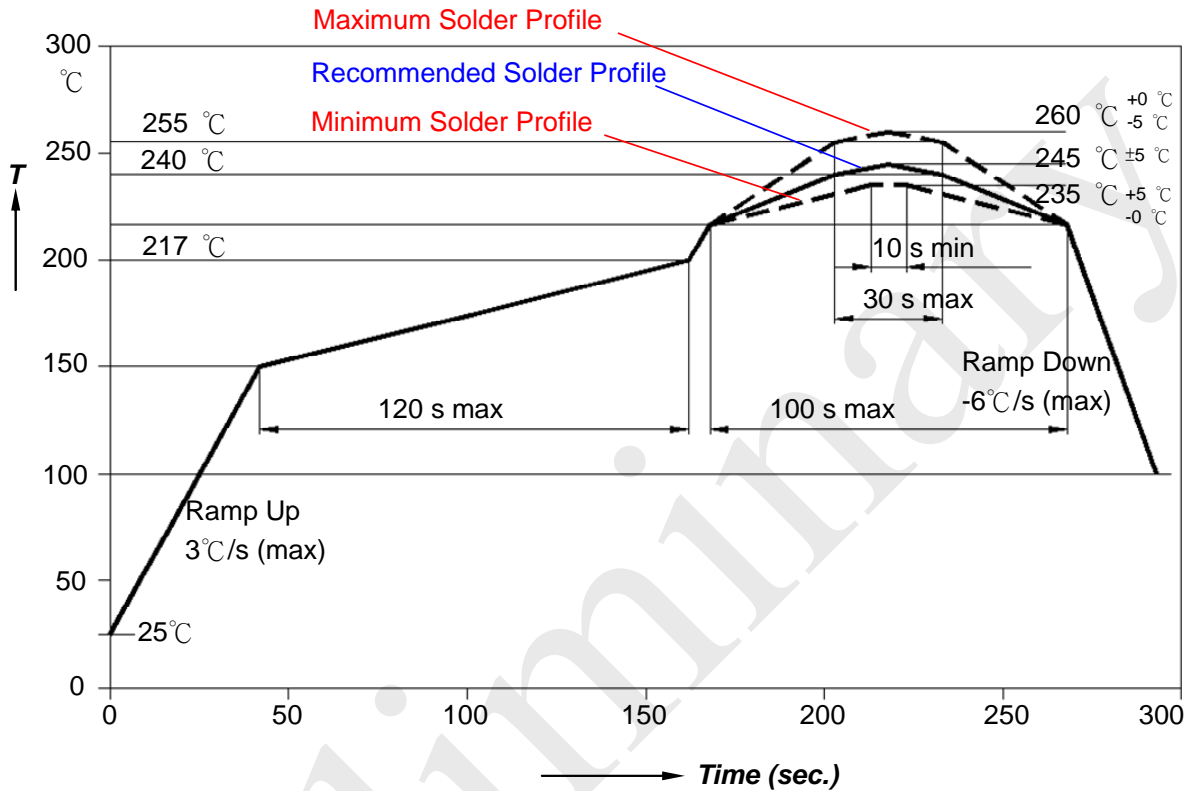


Typical Forward I-V Characteristics, $T_j=25^\circ\text{C}$



Recommended Soldering Profile

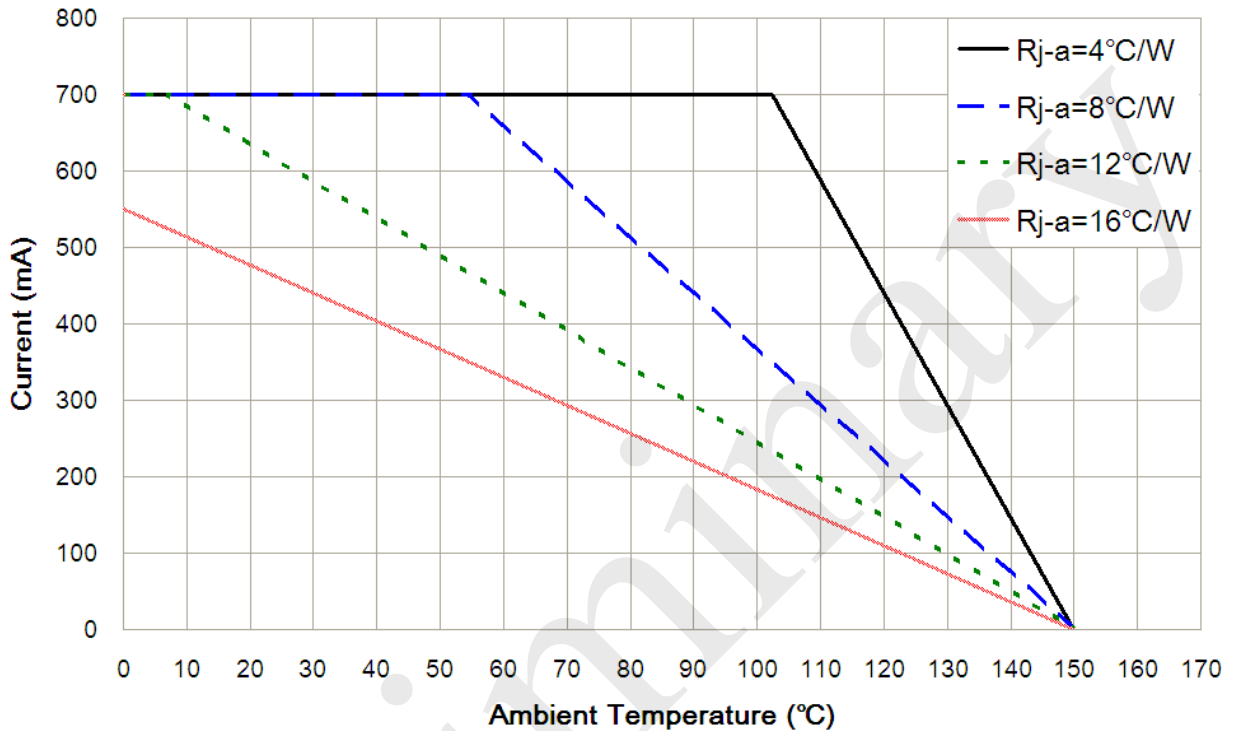
The LEDs can be soldered using the parameters listed below. As a general guideline, the users are suggested to follow the recommended soldering profile provided by the manufacturer of the solder paste. Although the recommended soldering conditions are specified in the list, reflow soldering at the lowest possible temperature is advised for the LEDs.



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average Ramp-up Rate (T _{smax} to T _p)	3°C/second max.	3°C/second max.
Preheat		
- Temperature Min(T _{smin})	100°C	150°C
- Temperature Max(T _{smax})	150°C	200°C
- Time(ts _{min} to ts _{max})	60-120 seconds	60-180 seconds
Time maintained above:		
- Temperature(T _l)	183°C	217°C
- Time(t _l)	60-150 seconds	60-150 seconds
Peak/classification Temperature(T _p)	215°C	260°C
Time within 5°C of actual Peak Temperature(tp)	10-30 seconds	20-40 seconds
Ramp-Down Rate	6°C/second max.	6°C/second max.
Time 25°C to Peak Temperature	6 minutes max.	8 minutes max.

Thermal Design

Thermal design of the end product is important. The thermal resistance between the junction and the solder point ($R_{\theta_{j-p}}$) and the end product should be designed to minimize the thermal resistance from the solder point to ambient in order to optimize the emitter life and optical characteristics. The maximum operation current is determined by the plot of Allowable Forward Current vs. Ambient Temperature.



The junction temperature can be correlated to the thermal resistance between the junction and ambient (R_{ja}) by the following equation.

$$T_j = T_a + R_{ja} * W$$

T_j : LED junction temperature

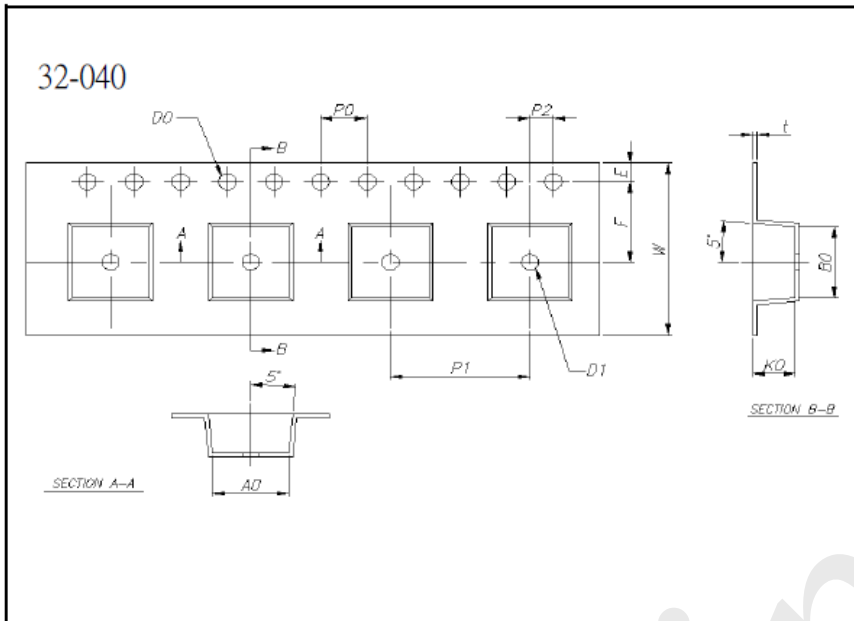
T_a : Ambient temperature

R_{ja} : Thermal resistance between the junction and ambient

W : Input power ($I_f * V_f$)

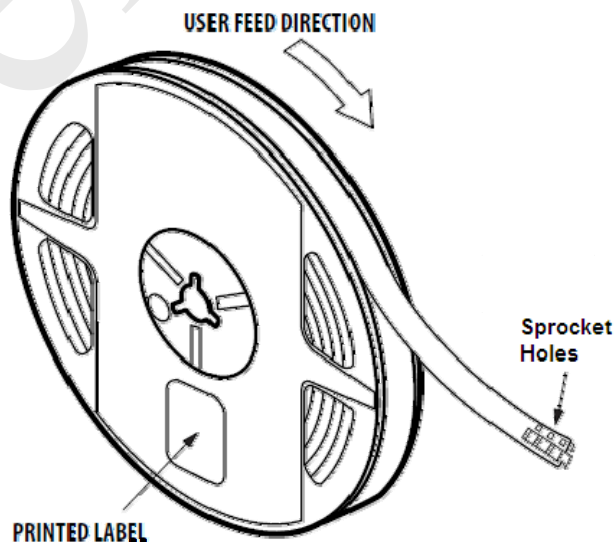
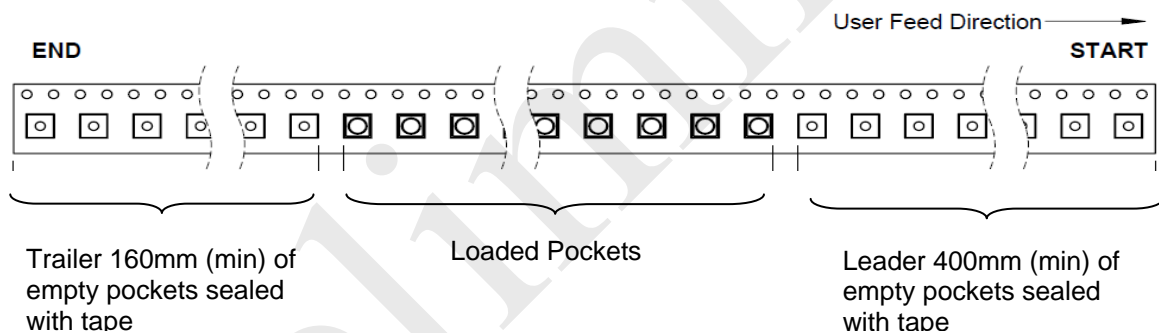
Packing information

Dimensions. (Unit: mm)



Item	Specification	Tol. (+/-)
W	16.00	± 0.20
E	1.75	± 0.10
F	7.50	± 0.10
D0	1.50	+0.10,-0
D1	1.50	± 0.10
P0	4.00	± 0.10
P1	12.00	± 0.10
P2	2.00	± 0.10
P0 x 10	40.00	± 0.20

t	0.35	± 0.05
A0	6.75	± 0.10
B0	6.65	± 0.10
K0	3.65	± 0.10



About Us

SemiLEDs is an innovative manufacturer of chip-level and packaged LEDs that enable today's advanced solid state lighting solutions. Fully ISO9001 certified, with state of the art fabrication facilities in Hsinchu Science Park, Taiwan, the company employs patented and proprietary technologies that deliver high performance with increased color stability and lumen maintenance. SemiLEDs visible- and ultraviolet-LEDs are found in a wide variety of general lighting applications, including street lights and commercial, industrial and residential architectural lighting, along with specialty industrial applications such as UV curing, medical/cosmetic, counterfeit detection, and horticulture.

SemiLEDs is a publicly traded company on NASDAQ Global Select Market (stock symbol "LEDS"). For investor information, please contact us at investors@semileds.com.

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